

Yue Yang

List of Publications by Year in descending order

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40
papers

1,161
citations

516710

16
h-index

677142

22
g-index

40
all docs

40
docs citations

40
times ranked

894
citing authors

#	ARTICLE	IF	CITATIONS
1	A novel framework for robust long-term object tracking in real-time. Machine Vision and Applications, 2019, 30, 529-539.	2.7	0
2	Real-time optical flow-based video stabilization for unmanned aerial vehicles. Journal of Real-Time Image Processing, 2019, 16, 1975-1985.	3.5	29
3	Data-driven identification and control of nonlinear systems using multiple NARMA-L2 models. International Journal of Robust and Nonlinear Control, 2018, 28, 3806-3833.	3.7	12
4	Long-term cooperative tracking using multiple unmanned aerial vehicles. , 2016, , .		1
5	Wide area surveillance of urban environments using multiple Mini-VTOL UAVs. , 2015, , .		6
6	Necessary and sufficient conditions for regional stabilisability of second-order switched linear systems with a finite number of subsystems. Automatica, 2014, 50, 931-939.	5.0	6
7	GeTe Liner Stressor Featuring Phase-Change- Induced Volume Contraction for Strain Engineering of Sub-50-nm p-Channel FinFETs: Simulation and Electrical Characterization. IEEE Transactions on Electron Devices, 2014, 61, 2647-2655.	3.0	3
8	High performance Ge CMOS with novel InAlP-passivated channels for future sub-10 nm technology node applications. , 2013, , .		11
9	Robust identification of piecewise affine systems from noisy data. , 2013, , .		0
10	Germanium–Tin (GeSn) p-Channel MOSFETs Fabricated on (100) and (111) Surface Orientations With Sub-400 Å²H₆Passivation, HfO₂Gate Dielectric, and Single TaN Metal Gate: A Common Gate Stack Technology for In_{0.7}Ga_{0.3}As and Ge_{1-x}Sn_xCMOS. IEEE Electron Device Letters, 2013, 34, 339-341.	3.9	94
11	Sub-400 Å²C Si₂H₆Passivation, HfO₂Gate Dielectric, and Single TaN Metal Gate: A Common Gate Stack Technology for In_{0.7}Ga_{0.3}As and Ge_{1-x}Sn_xCMOS. IEEE Transactions on Electron Devices, 2013, 60, 1640-1648.	3.0	23
12	Germanium Multiple-Gate Field-Effect Transistor With In Situ Boron-Doped Raised Source/Drain. IEEE Transactions on Electron Devices, 2013, 60, 2135-2141.	3.0	12
13	$\text{Ni}(\text{Ge}_{1-x}\text{Sn}_x)$ Ohmic Contact Formation on N-Type $\text{Ge}_{1-x}\text{Sn}_x$ Using Selenium or Sulfur Implant and Segregation. IEEE Transactions on Electron Devices, 2013, 60, 746-752.	3.0	26
14	Tunneling field-effect transistor with Ge/In _{0.53} Ga _{0.47} As heterostructure as tunneling junction. Journal of Applied Physics, 2013, 113, .	2.5	23
15	Germanium-Tin (GeSn) N-channel MOSFETs with low temperature silicon surface passivation. , 2013, , .		0
16	(110)-oriented germanium-tin (Ge^{inf>0.97}Sn^{inf>0.03}) P-channel MOSFETs. , 2013, , .		2
17	Germanium-Tin P-Channel Tunneling Field-Effect Transistor: Device Design and Technology Demonstration. IEEE Transactions on Electron Devices, 2013, 60, 4048-4056.	3.0	52
18	Ge _{0.97} Sn _{0.03} p-channel metal-oxide-semiconductor field-effect transistors: Impact of Si surface passivation layer thickness and post metal annealing. Journal of Applied Physics, 2013, 114, 044510.	2.5	43

#	ARTICLE	IF	CITATIONS
19	Asymmetrically strained high performance Germanium gate-all-around nanowire p-FETs featuring 3.5 nm wire width and contractible phase change liner stressor (Ge ₂ Sb ₂ Te ₅). , 2013, , .		4
20	Simulation of tunneling field-effect transistors with extended source structures. Journal of Applied Physics, 2012, 111, 114514.	2.5	15
21	Electronic band structure and effective mass parameters of Ge _{1-x} Sn _x alloys. Journal of Applied Physics, 2012, 112, .	2.5	194
22	High-Performance Germanium Ω -Gate MuGFET With Schottky-Barrier Nickel Germanide Source/Drain and Low-Temperature Disilane-Passivated Gate Stack. IEEE Electron Device Letters, 2012, 33, 1336-1338.	3.9	20
23	(NH ₄) ₂ S Passivation for High Mobility Germanium-Tin (GeSn) p-MOSFETs. , 2012, , .		1
24	High performance Ω -gate Ge FinFET featuring low temperature Si ₂ H ₆ passivation and implantless Schottky-barrier NiGe metallic Source/Drain. , 2012, , .		2
25	Germanium-Tin n^+p Junction Formed Using Phosphorus Ion Implant and 400 $^{\circ}\text{C}$ Rapid Thermal Anneal. IEEE Electron Device Letters, 2012, 33, 1529-1531.	3.9	17
26	Towards high performance Ge _{1-x} Sn _x and In _{0.7} Ga _{0.3} As CMOS: A novel common gate stack featuring sub-400 \AA Si ₂ H ₆ passivation, single TaN metal gate, and sub-1.3 nm EOT. , 2012, , .		5
27	Towards direct band-to-band tunneling in P-channel tunneling field effect transistor (TFET): Technology enablement by Germanium-tin (GeSn). , 2012, , .		42
28	Metal stanogermanide contacts with enhanced thermal stability for high mobility germanium-tin field-effect transistor. , 2012, , .		2
29	PBTI characteristics of N-channel tunneling field effect transistor with HfO ₂ gate dielectric: New insights and physical model. , 2012, , .		5
30	Sufficient and necessary conditions for the stability of second-order switched linear systems under arbitrary switching. International Journal of Control, 2012, 85, 1977-1995.	1.9	19
31	Dopant Segregation and Nickel Stanogermanide Contact Formation on n^+p Ge _{0.947} Sn _{0.053} Source/Drain. IEEE Electron Device Letters, 2012, 33, 634-636.	3.9	35
32	High-mobility germanium-tin (GeSn) P-channel MOSFETs featuring metallic source/drain and sub-370 \AA Si ₂ H ₆ process modules. , 2011, , .		39
33	Feedback stabilization for planar switched linear systems with two subsystems under arbitrary switching. , 2011, , .		3
34	Electrostatics of Ultimately Thin-Body Tunneling FET Using Graphene Nanoribbon. IEEE Electron Device Letters, 2011, 32, 431-433.	3.9	11
35	Bias temperature instability (BTI) characteristics of graphene Field-Effect Transistors. , 2011, , .		7
36	Silicon-based tunneling field-effect transistor with elevated germanium source formed on (110) silicon substrate. Applied Physics Letters, 2011, 98, 153502.	3.3	58

#	ARTICLE	IF	CITATIONS
37	Tunneling Field-Effect Transistor: Capacitance Components and Modeling. IEEE Electron Device Letters, 2010, 31, 752-754.	3.9	213
38	Enhancement of TFET performance using dopant profile-steepening implant and source dopant concentration engineering at tunneling junction. , 2010, , .		10
39	SPICE Behavioral Model of the Tunneling Field-Effect Transistor for Circuit Simulation. IEEE Transactions on Circuits and Systems II: Express Briefs, 2009, 56, 946-950.	3.0	20
40	Tunneling Field-Effect Transistor: Effect of Strain and Temperature on Tunneling Current. IEEE Electron Device Letters, 2009, 30, 981-983.	3.9	96